WHAT IS CLAIMED IS:

1. A method of forming an individually patterned layer in a plurality of regions of a substrate, comprising the steps of:

disposing between said substrate and a layer material source a mask including an opening corresponding to one or more of the plurality of regions where said layer is formed; and

causing relative movement between said mask and said layer material source, and said substrate, and causing a material scattered from said layer material source to attach to said substrate through said opening, thereby forming said individually patterned layer.

2. A method according to claim 1, wherein

said layer material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said layer material source, and said substrate.

3. A method according to claim 2, wherein

said linearly extending source is formed by a plurality of layer material sources arranged adjacent to each other.

4. A method according to claim 1, wherein

said layer is an electroluminescent layer formed between first and second electrodes, and

said layer material is an electroluminescent material.

5. A method according to claim 4, wherein

said electroluminescent material is an organic material scattered from said layer material source by evaporation and attached to said substrate, thereby forming said electroluminescent layer.

6. A method according to claim 1, wherein

a semiconductor material is used for said mask.

7. A method of forming an individually patterned layer in a plurality of regions of a substrate, comprising the steps of:

disposing between said substrate and a layer material source a mask having a smaller area than said substrate and including an opening corresponding to one or more of the plurality of regions where said layer is formed; and

causing relative movement between said mask and said layer material source, and said substrate, and causing a material scattered from said layer material source to attach to said substrate through said opening, thereby forming said individually patterned layer.

8. A method according to claim 7, wherein

said layer material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said layer material source, and said substrate.

9. A method according to claim 8, wherein

said linearly extending source is formed by a plurality of layer material sources arranged adjacent to each other.

10. A method according to claim 7, wherein

a semiconductor material is used for said mask.

11. A manufacturing method of a color emissive device including, on a substrate, a self-emissive element having a first electrode, an emissive material layer for each color, and a second electrode, for each of a plurality of pixels, said method comprising the steps of:

disposing between said substrate and an emissive material source a mask including an opening at a position corresponding to a region for forming the emissive material layer of one or more of said plurality of pixels of said substrate; and

sliding a relative position between said mask and said emissive material source, and said substrate by a predetermined pitch corresponding to a size of the pixel of said substrate, and causing an emissive material to attach to a predetermined region of said substrate through said mask, thereby forming the emissive material layer.

12. A manufacturing method of a color emissive device according to claim 11, wherein

said substrate is slid in two directions of said substrate perpendicular to each other by a pitch corresponding to an

arrangement of said pixels for a same color.

13. A manufacturing method of a color emissive device according to claim 11, wherein

said substrate is slid in one direction of said substrate by a pitch corresponding to an arrangement of said pixels for a same color.

14. A manufacturing method of a color emissive device according to claim 11, wherein

said emissive material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said emissive material source, and said substrate.

15. A manufacturing method of a color emissive device according to claim 14, wherein

said linearly extending source is formed by a plurality of emissive material sources arranged adjacent to each other.

16. A manufacturing method of a color emissive device according to claim 11, wherein

said self-emissive element is an electroluminescent element.

17. A manufacturing method of a color emissive device according to claim 11, wherein

said emissive device is a display device for displaying

an image with a plurality of pixels.

18. A manufacturing method of a color emissive device according to claim 11, wherein

a semiconductor material is used for said mask.

19. A manufacturing method of a color emissive device including, on a substrate, a self-emissive element having a first electrode, an emissive material layer for each color, and a second electrode, for each of a plurality of pixels, said method comprising the steps of:

disposing between said substrate and an emissive material source a mask including an opening at a position corresponding to a region for forming the emissive material layer of one or more of said plurality of pixels of said substrate, and having a smaller area than said substrate to cover one or more of said plurality of pixels on said substrate; and

sliding a relative position between said mask and said emissive material source, and said substrate by a predetermined pitch corresponding to a size of the pixel of said substrate, and causing an emissive material to attach to a predetermined region of said substrate through said mask, thereby forming the emissive material layer.

20. A manufacturing method of a color emissive device according to claim 19, wherein

said substrate is slid in two directions of said substrate perpendicular to each other by a pitch corresponding to an

arrangement of said pixels for a same color.

21. A manufacturing method of a color emissive device according to claim 19, wherein

said substrate is slid in one direction of said substrate by a pitch corresponding to an arrangement of said pixels for a same color.

22. A manufacturing method of a color emissive device according to claim 19, wherein

said emissive material source is a linearly extending source elongated in a direction perpendicular to a direction of the relative movement between said mask and said emissive material source, and said substrate.

23. A manufacturing method of a color emissive device according to claim 22, wherein

said linearly extending source is formed by a plurality of emissive material sources arranged adjacent to each other.

24. A manufacturing method of a color emissive device according to claim 19, wherein

a semiconductor material is used for said mask.

25. A manufacturing method of a display device including, on a substrate, a self-emissive element having a first electrode, an emissive material layer for each color, and a second electrode, for each of a plurality of pixels, said method

comprising the steps of:

disposing between said substrate and an emissive material source a mask including an individual opening for each pixel corresponding to a region for forming the emissive material layer individually patterned for each of said plurality of pixels; and

sliding a relative position between said emissive material source and said substrate and causing an emissive material to attach to a predetermined region of said substrate through the opening of said mask, thereby forming the emissive material layer.

26. A manufacturing method of a display device according to claim 25, wherein

said emissive material source is a linearly extending source elongated in one direction.